

24 February 2004

Updated Search

09/782,216

L Number	Hits	Search Text	DB	Time stamp
-	0	476526.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 11:13
-	1	6547937.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 14:25
-	152	204/\$.ccls. and (cleaning adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/28 16:24
-	17	(204/\$.ccls. and (cleaning adj electrode)) and (microelectronic or wafer or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/28 16:24
-	12396	204/\$.ccls. and (anode same cathode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 10:53
-	1	782216.apn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:12
-	59395	204/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:12
-	35240	205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	83968	204/\$.ccls. 205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	10782	(204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:13
-	1310	((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((second or secondary or another or additional) near (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:14
-	574	((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean\$5 or strip\$5 deposit) near2 (anode or cathode or electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18

-	174	(((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((second or secondary or another or additional) near (electrode or cathode or anode))) and (((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean\$5 or strip\$5 deposit) near2 (anode or cathode or electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18
-	93	(((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((second or secondary or another or additional) near (electrode or cathode or anode))) and (((204/\$.ccls. 205/\$.ccls.) and (microelectronic or semiconductor or wafer)) and ((clean\$5 or strip\$5 deposit) near2 (anode or cathode or electrode)))) and (etch\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 13:18
-	462	205/640,646,648,652,686.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 14:26
-	98	205/640,646,648,652,686.ccls. and clean\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-	744	204/224m.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-	2427	204/275.1,237,242,280.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:02
-	3092	204/224m.ccls. 204/275.1,237,242,280.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:10
-	167	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and ((electrochem\$7 or electrol\$7 or (electro adj chem\$7)) near2 (etch\$5 or polish\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:12
-	100	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and (electropolish\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:12
-	57	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and ((electropolish\$5) with (electrode or anode or cathode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 14:28
-	87	(204/224m.ccls. 204/275.1,237,242,280.ccls.) and (((electrochem\$7 or electrol\$7 or (electro adj chem\$7)) near2 (etch\$5 or polish\$3)) with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:21
-	809	(204/\$.ccls. 205/\$.ccls.) and (((builld or built) adj up) or deposit\$5 or collect\$3) with (electrode or cathode or electrode) with (distance or gap or spacing))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/01 09:03

-	179	(204/\$.ccls. 205/\$.ccls.) and (((((build or built) adj up) or deposit\$5 or collect\$3) with (electrode or cathode or electrode) with (distance or gap or spacing)) same (remov\$4 or clean\$3 or strip\$4 or etch\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:25
-	804	(204/\$.ccls. 205/\$.ccls.) and (((((build or built) adj up) or deposit\$5 or collect\$3) with (electrode or cathode or electrode) with (distance or gap or spacing)) same ((remov\$4 or clean\$3 or strip\$4 or etch\$4) with ((build or built) adj up) or deposit\$5 or collect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:28
-	133	(204/\$.ccls. 205/\$.ccls.) and (((((build or built) adj up) or deposit\$5 or collect\$3) with (electrode or cathode or electrode) with (distance or gap or spacing)) same ((remov\$4 or clean\$3 or strip\$4 or etch\$4) with (((build or built) adj up) or deposit\$5 or collect\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/29 15:29
-	3	((("6500324") or ("6174425")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 09:33
-	8867	204/\$.ccls. and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:30
-	2347	(204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 10:31
-	1056	(204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 13:15
-	65	((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with anode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 13:17
-	75	((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (mesh with (anode or porous))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:14
-	160	((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with (mesh or porous))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:15

-	110	((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with rotat\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:15
-	125	((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:16
-	60	(((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode near2 (rotat\$5 or mov\$7))) and (((204/\$.ccls. and (microelectronic or semiconductor or wafer)) and ((anode or cathode or electrode) with (fluid or solution or electrolyte) with (conduit or path or pathway or port or passage or passageway or flow or opening or inlet or outlet))) and (anode with (mesh or porous)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:23
-	2	6197182.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:35
-	1349	204/\$.ccls. and (solution with ((rins\$4 or clean\$5) and (electroplat\$5 or electroly\$6 or plating)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:39
-	765	(204/\$.ccls. and (solution with ((rins\$4 or clean\$5) and (electroplat\$5 or electroly\$6 or plating)))) not rinsed!	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:40
-	3	(((("6103096") or ("5614076") or ("5531874") or ("5486282") or ("5543032") or ("5536388") or ("5567300") or ("5284554")).PN.) and ((rins\$ or clean\$) with (plating or electroly\$5 or electroplat\$5))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:43
-	5	6103096.URPN.	USPAT	2003/07/30 14:44
-	15	(((("6103096") or ("5614076") or ("5531874") or ("5486282") or ("5543032") or ("5536388") or ("5567300") or ("5284554")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:49
-	29	5567300.URPN.	USPAT	2003/07/30 14:47

-	20	5543032.URPN.	USPAT	2003/07/30 14:48
-	6	5536388.URPN.	USPAT	2003/07/30 14:48
-	15	5486282.URPN.	USPAT	2003/07/30 14:48
-	19	5284554.URPN.	USPAT	2003/07/30 14:48
-	62	5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:49
-	0	(5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.) and (clean\$5 with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:50
-	26	(5567300.URPN. 5543032.URPN. 5536388.URPN. 5486282.URPN. 5284554.URPN.) and (remov\$5 with (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:55
-	83968	204/\$.ccls. 205/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/30 14:56
-	3	(204/\$.ccls. 205/\$.ccls.) and (electrochem\$7 near (micromachin\$5 or machin\$5)) and (clean\$ near (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:32
-	295	204/275.1,237,242,280.ccls. and (titanium with (platinum or platinized))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:05
-	83	(204/275.1,237,242,280.ccls. and (titanium with (platinum or platinized))) and (microelectronic or semiconductor or wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/30 15:06
-	18	((("5312532") or ("5344491") or ("5421987") or ("5431421") or ("5516412") or ("5925226") or ("6001235") or ("6228231") or ("6251250"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 11:08
-	8	ep-0343502-\$.did. ep-0726698-\$.did. jp-62297494-\$.did. jp-62297495-\$.did. jp-1120827-\$.did. jp-5175158-\$.did. jp-6260468-\$.did. jp-7211724-\$.did. jp-7284738-\$.did. jp-10172974-\$.did. jp-11092993-\$.did. jp-2000017480-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/31 11:11

-	840	(204/\$.ccls. 205/\$.ccls.) and (((build or built) adj up) or deposit\$5 or collect\$3) with (electrode or cathode or electrode) with (distance or gap or spacing))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/08/01 09:04
-	2	6328872.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 13:32
-	22	("3395092" "3436259" "3890746" "3959089" "4153523" "4395320" "4610772" "4919769" "5024735" "5171412" "5429733" "5558568" "5650039" "5692947" "5755859" "5807165" "5833820" "5863412" "5930669" "5933753" "6004880" "6017820").PN.	USPAT	2004/02/24 13:36
-	19	("2751340" "2859166" "3880725" "4148707" "4304641" "4420382" "4421627" "4466864" "4678545" "4720329" "4879007" "5084153" "5135636" "5149419" "5230743" "5312532" "5332487" "5582708" "5620581").PN.	USPAT	2004/02/24 14:02
-	7	6174425.URPN.	USPAT	2004/02/24 14:06
-	360	204/222.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:12
-	817	204/224r.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:12
-	1158	204/222.ccls. 204/224r.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:13
-	13	(204/222.ccls. 204/224r.ccls.) and (clean\$3 near (electrode or anode or cathode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:20
-	23	(204/222.ccls. 204/224r.ccls.) and ((electropolish\$5) with (electrode or anode or cathode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/02/24 14:28
-	0	(204/222.ccls. 204/224r.ccls.) and (electrochem\$7 near (micromachin\$5 or machin\$5)) and (clean\$ near (electrode or cathode or anode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/24 14:32